

BC307/308/309

Switching and Amplifier Applications

• Low Noise: BC309



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Parameter Value	
V _{CES}	Collector-Emitter Voltage		
	: BC307	-50	V
	: BC308/309	-30	V
V_{CEO}	Collector-Emitter Voltage		
	: BC307	-45	V
	: BC308/309	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
l _C	Collector Current (DC)	-100	mA
P_{C}	Collector Power Dissipation	500	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

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C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -2mA$, $I_B = 0$				
	: BC307		-45			V
	: BC308/309		-25			V
BV _{CES}	Collector-Emitter Breakdown Voltage	I _C = -10μA, V _{BE} =0				
	: BC307		-50			V
	: BC308/309		-30			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = -10μA, I _C =0	-5			V
I _{CES}	Collector Cut-off Current					
020	: BC307	V _{CE} = -45V, V _{BE} =0		-2	-15	nA
	: BC308/309	V _{CE} = -25V, V _{BE} =0		-2	-15	nA
h _{FE}	DC Current Gain	V _{CE} = -5V, I _C = -2mA	120		800	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -10mA, I _B = -0.5mA			-0.3	V
	_	I _C = -100mA, I _B = -5mA		-0.5		V
V _{BE} (sat)	Collector-Base Saturation Voltage	I _C = -10mA, I _B = -0.5mA		-0.7		V
		I _C = -100mA, I _B = -5mA		-0.85		V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} = -5V, I _C = -2mA	-0.55	-0.62	-0.7	V
f _T	Current Gain Bandwidth Product	V _{CE} = -5V, I _C = -10mA, f=50MHz		130		MHz
C _{ob}	Output Capacitance	V _{CB} = -10V, I _E =0, f=1MHz			6	pF
C _{ib}	Input Capacitance	V _{EB} = -0.5V, I _C =0, f=1MHz		12		pF
NF	Noise Figure					
	: BC307/308	$V_{CE} = -5V, I_{C} = -0.2mA,$			10	dB
	: BC309	R _G =2KΩ, f=1KHz			4	dB
	: BC309	$V_{CE} = -5V, I_{C} = -0.2mA$		2	4	dB
		R _G =2KΩ, f=30~15KHz				

h_{FE} Classification

Classification	А	В	С
h _{FE}	120 ~ 220	180 ~ 460	380 ~ 800

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Typical Characteristics

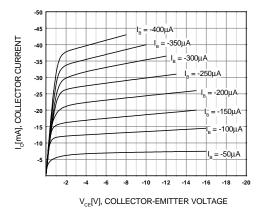


Figure 1. Static Characteristic

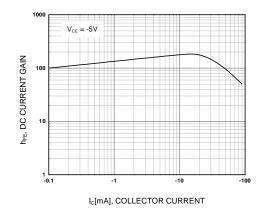


Figure 2. DC current Gain

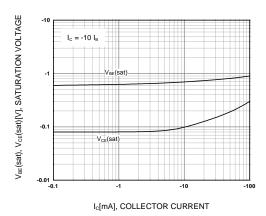


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

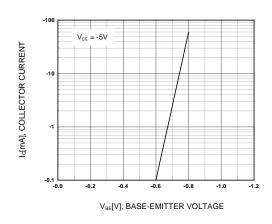


Figure 4. Base-Emitter Capacitance

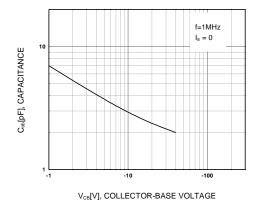


Figure 5. Collector Output Capacitance

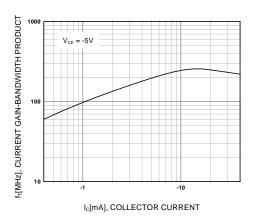
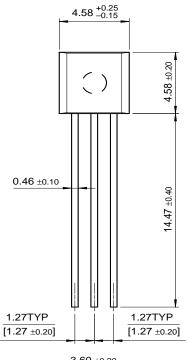


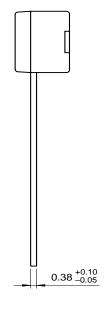
Figure 6. Current Gain Bandwidth Product

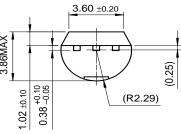
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Package Dimensions

TO-92







Dimensions in Millimeters

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CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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